风光欣技术资料

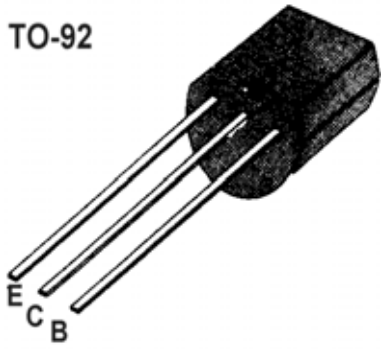
S8098

—NPN silicon —

■■**APPLICATION**：POWER AMPLIFIER APPLICATION,SWITCH APPLICATION.

■■**MAXIMUM RATINGS**（Ta＝25℃）

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CBO}	60	V
Collector-emitter voltage	V_{CEO}	60	V
Emitter-base voltage	V_{EBO}	6	V
Collector current	I_C	500	mA
Collector Power Dissipation	P_C	600	mW
Junction Temperature	T_J	150	℃
Storage Temperature Range	Tstg	－55~150	℃



■■**ELECTRICAL CHARACTERISTICS**（Ta=25℃）

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h_{FE}	100		300		V_{CE}= 5V，Ic= 1mA
Collector Cut-off Current	I_{CBO}			0.1	μA	V_{CB}= 60V，I_E=0
Emitter Cut-off Current	I_{EBO}			0.1	μA	V_{EB}= 6V，Ic=0
Collector-Base Breakdown Voltage	BV_{CBO}	60			V	Ic= 0.1mA，I_E=0
Collector-Emitter Breakdown Voltage	BV_{CEO}	60			V	Ic= 1mA，I_B=0
Emitter-Base Breakdown Voltage	BV_{EBO}	6			V	I_E= 0.1mA，Ic=0
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			0.3	V	Ic= 100mA，I_B= 10mA
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			1.0	V	Ic= 100mA，I_B= 10mA
Gain bandwidth product	f_T	150			MHz	Ic= 10mA，V_{CE}= 5V
Common Base Output Capacitance	Cob			4.5	PF	V_{CB}= 5V，I_E=0，f = 1MHz

■■h_{FE} **Classification**

Classification	
h_{FE}	100~300